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A cross-sectional view of a multi-layered structure 22B. The structure consists of several layers: a top layer 24(17), a middle layer 23(13) with a central core 8 and side regions 15, and a bottom layer 22(7). The bottom layer 22(7) is supported by a base 22B. The structure is shown with multiple repeating units.

This cross-sectional view shows two active regions of the semiconductor device. Each region consists of a substrate (22(7)) with a well (21(21A)) and a channel (23(13)). The channel is covered by a gate stack (24(17)) which includes a gate dielectric (18) and a gate electrode (15). The gate electrode is connected to a gate line (8). The device is shown with two such regions separated by a trench.

FIG. 3

